

isc Silicon NPN Power Transistor

2SC5252

DESCRIPTION

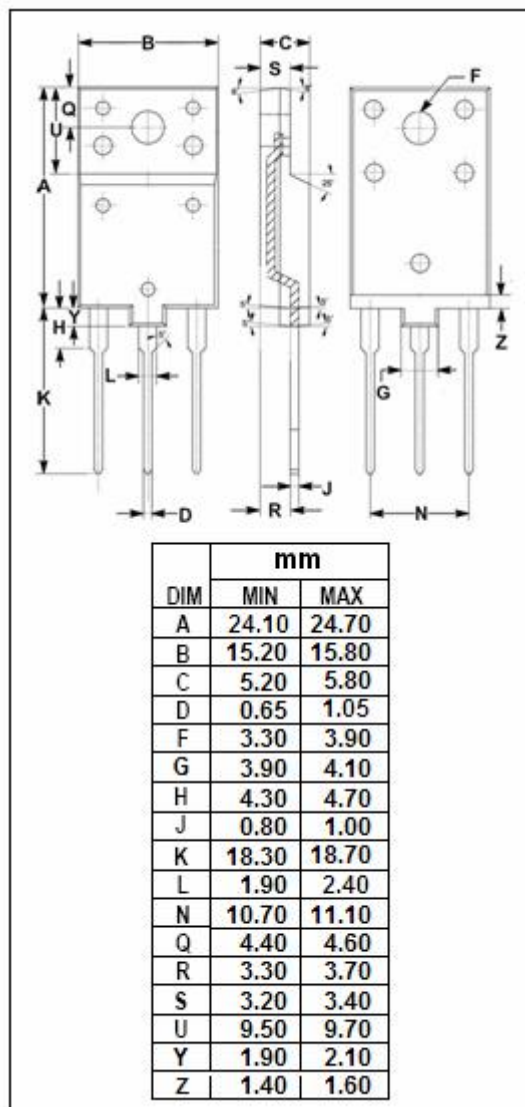
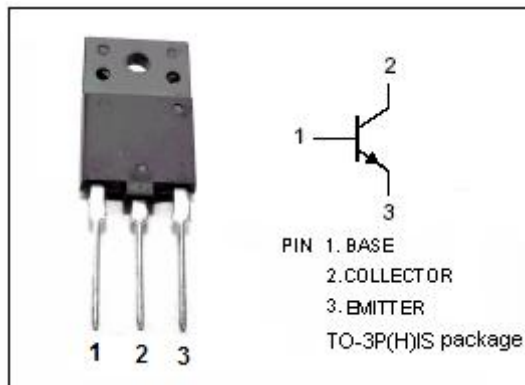
- High speed switching
- High breakdown voltage
- VCBO = 1500 V

APPLICATIONS

- Character display horizontal deflection output

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	1500	V
V _{CEO}	Collector-Emitter Voltage	800	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current- Continuous	15	A
I _{CM}	Collector Current-Peak	30	A
P _C	Collector Power Dissipation @ T _C =25°C	50	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



isc Silicon NPN Power Transistor**2SC5252****ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=10\text{mA}; I_B=0$	800			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=10\text{A}; I_B=3\text{A}$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=10\text{A}; I_B=3\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=1500\text{V}; I_E=0$			0.5	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=6\text{V}; I_C=0$			1	mA
h_{FE-1}	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	8		35	
h_{FE-2}	DC Current Gain	$I_C=8\text{A}; V_{CE}=5\text{V}$	3		6	
f_T	Current-Gain—Bandwidth Product	$I_C=0.1\text{A}; V_{CE}=5\text{V}; f_{test}=1.0\text{MHz}$		5		MHz